

# Authors

## Joseph A. Aboaf

*IBM Thomas J. Watson Research Center, Yorktown Heights, New York*

Engaged in the development of thin films for variable threshold field effect transistors. Ph.D. degree in Chemistry, University of Milan, Italy, 1959. Research Assistant and lecturer, University of London, England, 1959-60. Research Member, Bausch & Lomb, Inc., Rochester, N. Y., 1960-63. Research Staff Member, IBM Thomas J. Watson Research Center, 1963-69. Advisory Engineer, Components Division, East Fishkill, 1969. Member, Electrochemical Society and American Ceramic Society.

## David S. Billingsley

*Data Processing Division, Scientific Center, Houston, Texas*

B.S. in Chemical Engineering, 1950; B.S. in Industrial Engineering and in Mechanical Engineering, 1956; M.S. in Chemical Engineering, 1958; Ph. D. in Chemical Engineering, 1961, all from Texas A & M University. Joined IBM in 1961 as a systems engineer in the Houston branch office, worked for the Federal Systems Division in the Real Time Computing Center at the NASA Manned Spacecraft Center in Houston from 1962 through 1964. Transferred to the staff of the Houston Scientific Center in 1964. Member, Phi Lambda Upsilon and Sigma Xi.

## Torsten P. A. Bohlin

*IBM Nordic Laboratory, Lidingö, Sweden*

Advisory Engineer at the IBM Nordic Laboratory. Civilingenjör in Physics, 1958; Teknologie Licentiat in Mathematics and Mathematical Statistics, 1965, Royal Institute of Technology (KTH), Stockholm, Sweden. Research Assistant in Applied Mathematics, 1957-58 and 1960-62 at KTH. Worked at the Research Institute of National Defence (FOA), Stockholm as a research engineer from 1958-60, on the principles of signal detection, radar tracking and interception. Joined the IBM Nordic Laboratory in 1962, where his field of research has been the theory and application of computer control in the process industries, in particular the problems of identification and adaptive control. Manager, Control Systems Theory Group, 1965-67. Member, TFF.

## Leo Esaki

*IBM Thomas J. Watson Research Center, Yorktown Heights, New York*

Manager of Applied Physics Group; appointed an IBM Fellow in 1967. B.S. in Physics, 1947; Ph.D. in Physics, 1959; both at the University of Tokyo. While at the Sony Corporation in Japan, his research resulted in the discovery of the tunnel diode. Became a Research Staff member at the IBM Research Center in 1960. Received Nishina Memorial Award, Asahi Press Award, Toyo Rayon Foundation Award and Japan Academy Award (1965); also Morris N. Liebmann Memorial Prize of the IEEE and the Ballantine Award of the Franklin Institute. Fellow, American Physical Society and IEEE.

## Joseph N. Gayles, Jr.

*Morehouse College, Atlanta, Georgia*

Associate Professor of Chemistry, Morehouse College. Research interests include laser scattering phenomena (primarily Brillouin and anisotropic Rayleigh scattering), molecular spectroscopy, laboratory automation, and the viscoelastic properties of polymers. A.B., 1958, Dillard University (New Orleans); Ph.D., in Chemistry, 1962, Brown University. Research Associate and Assistant Professor at Oregon State University, 1963; Assistant Professor of Chemistry and Woodrow Wilson Teaching Fellow, Morehouse College (Atlanta), 1964-66; summer associate with the Quantum Chemistry Group, University of Uppsala (Sweden), 1965. Associated with the IBM San Jose Research Laboratory, 1966-69. Member, American Chemical Society and American Physical Society.

## William L. Honzik

*Sullivan Associates, Santa Clara, California*

B.S. in Physics, 1969, University of Santa Clara, California. Joined IBM Research in March 1968 and remained there as student employee until April 1969. Student Member, American Physical Society.

## Robert E. Jones, Jr.

*Systems Development Division, San Jose, California*

A.B. in Chemistry, 1953, Columbia University; Ph.D. in Chemistry, 1957, University of California at Berkeley. He is currently engaged in technical planning.

## Sol Krongelb

*IBM Thomas J. Watson Research Center, Yorktown Heights, New York*

Engaged in studying the adhesive properties of material interfaces. B.S. in Engineering Physics, 1953, New York University; M.S., 1955, and Ph.D. in Physics, 1958, Massachusetts Institute of Technology. Joined IBM Research in 1958 and has done work on parametric circuits, tunnel diodes, deposition processes for insulating films, and the properties of oxides and semiconductor-oxides interfaces. Member, American Physical Society, IEEE, Tau Beta Pi and Sigma Xi.

## Solomon L. Levine

*Systems Development Division, Poughkeepsie, New York*

Currently working in the analytical laboratory of a materials technology group on a variety of chemically related materials problems. B.S., 1961, Rensselaer Polytechnic Institute; Ph.D., 1966, University of Rhode Island, both in Chemistry. Joined IBM in 1965 in Burlington as a materials manufacturing engineer.

## James Overmeyer

*Components Division, East Fishkill, New York*

Engaged in reliability evaluation of semiconductor devices. B.S. in Physics, 1949, Lehigh University. Joined IBM Research in 1954 and worked in magnetism research, chiefly electron spin resonance. Transferred to the Components Division in 1965. Member, Phi Beta Kappa and American Physical Society.

**Peter J. Price**

*Watson Laboratory, New York, New York*

Research staff member, solid state physics. Ph.D., Cambridge, 1951. Subsequently, research assistant to the late Fritz London at Duke University, and a member of the Institute for Advanced Study at Princeton. Joined IBM at the Watson Research Laboratory at Columbia University in 1953. Fellow, American Physical Society.

**Sidney S. Russell**

*Components Division, East Fishkill, New York*

Engaged in quality engineering studies, specializing in resistor and capacitor components. Associate in Electronic Technology, 1959, Flint Junior College, Michigan; B.S. in Applied Electronics, 1962, University of Michigan. Inspection Group Leader at Bendix Systems Division 1959-62 and Procurement Quality Engineer at Honeywell Aero, Florida Division, 1963-66. Joined IBM Components Division, Procurement Quality Engineering Staff, in 1967.

**Geraldine C. Schwartz**

*Components Division, East Fishkill, New York*

B.A., Brooklyn College, 1943; M.A. and Ph.D. in Physical Chemistry, 1945 and 1948, respectively, Columbia University. NIH Post-Doctoral Fellowship 1948-1950. Before coming to IBM, she was Assistant Professor of Chemistry at Bard College. She joined the IBM Components Division at Poughkeepsie in 1964 and has worked on a variety of thin film problems. She is currently engaged in development of thin film technology for integrated circuits. Member, Sigma Xi, RESA, AVS, and ECS.

**Thomas O. Sedgwick**

*IBM Thomas J. Watson Research Center, Yorktown Heights, New York*

Manager of Exploratory Thin Film Group since 1965; engaged in studies of semiconductor surface electronic properties and vapor transport reactions. B.S. in Chemistry, University of Massachusetts, 1955; Ph.D. in Chemistry, Polytechnic Institute of Brooklyn, 1962; Postdoctoral Fellowship (Fulbright, German Federal Government) University of Munich, 1961-62; Process Development Chemist, American Cyanamid Co., Stamford Research Labs., 1955-57. Member, Electrochemical Society.

**Raphael Tsu**

*IBM Thomas J. Watson Research Center, Yorktown Heights, New York*

Research staff member; theoretical and experimental studies in the broad area of semiconductor physics. B.S., 1956, University of Dayton; M.S. and Ph.D., 1957 and 1960, respectively, Ohio State University, all in Electrical Engineering. Research Associate at the Antenna Laboratory working on the theory and experiments on the scattering matrix while completing Ph.D. Worked on electron-phonon interactions and diffraction delay lines at the Bell Telephone Laboratories, 1961-64. Assistant Professor of Physics at Trinity University, 1964-66. Joined IBM in 1966. Member, American Physical Society, Sigma Xi and Sigma Pi Sigma.

**Duane O. Wilson**

*IBM Research Laboratory, San Jose, California*

B.A. in Physics, 1968, University of California at Irvine. Joined IBM Research in 1968 as a Research Assistant. Currently working on experiments dealing with electron paramagnetic resonance and far-infrared Michelson interferometry.

• *Symposium on Instabilities in Semiconductors*

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